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## M1Or3A-06 [Invited]: Jc enhancement and changes in the pinning mechanisms in newly alloyed Nb<sub>3</sub>Sn for FCC application

*Monday, 22 July 2019 17:40 (20 minutes)*

The construction of the Future Circular Collider (FCC) has very stringent requirements for Nb<sub>3</sub>Sn conductor critical current density,  $J_{c}$ , with a target non-Cu  $J_{c}(16T, 4.2K)$  of at least 1500 A/mm<sup>2</sup>. Nowadays the best commercial Nb<sub>3</sub>Sn strands can only reach 1300 A/mm<sup>2</sup>, consequently it will be necessary to significantly increase the high field  $J_{c}$ . To meet this challenge requires new approaches that can introduce additional pinning centers while maintaining a high irreversibility field,  $H_{irr}$ . In this work, we focus on Nb<sub>3</sub>Sn wires prepared using Nb-Ta-Zr and Nb-Ta-Hf alloys. Both Zr and Hf had been partially investigated in the '80 and '90 but only recently it has been shown that greatly enhanced pinning can be obtained in Nb<sub>3</sub>Sn with Zr or Hf, while maintaining high  $H_{irr}$  by incorporating Ta doping. In the Zr case, an internal oxygen source (SnO<sub>2</sub>) is required, and ZrO<sub>2</sub> nanoparticles have been shown to form in the Nb<sub>3</sub>Sn. However, we find that  $F_{p}$  and  $J_{c}$  at high field can be further improved with Hf additions without supplemental oxygen. The introduction of a significant point defect pinning contribution increases the maximum of  $F_{p}$  by more than a factor 2 and shifts its peak position from 4.6 to 5.8 T with respect to Ta-only doped wires. This leads to a layer  $J_{c}(16T, 4.2K)$  of about 3710 A/mm<sup>2</sup>, corresponding to a potential non-Cu  $J_{c}(16T, 4.2K)$  of 2230 A/mm<sup>2</sup>. We will also discuss the sensitivity of these properties to heat treatment, the different  $H_{irr}$  and  $F_{p}$  behavior with respect to standard Ta/Ti-doped conductors and the recent high field characterizations of newer alloyed wires.

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